ABSTRACT

Blankmask for EUV lithography has a reflective film formed on a substrate and an absorbing film formed on the reflective film. The absorbing film contains tantalum (Ta) and antimony (Sb). The absorbing film has a composition ratio of Ta:Sb = 2:8 ~ 6:4 at%. The absorbing film with a high extinction coefficient (k) allows for the thin film deposition of the absorbing film, reducing the Shadowing Effect and 3D Effect.

FIG. 2